## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Sheldon Aronowitz and	)		
Vladimir Zubkov	)		
	)		
Filed: Herewith	)		
	) (	Group Art Unit:	Unknown
Serial Number: Divisional of 09/792,691	)		
	)	Examiner: Unkn	own
Title: "A Low Dielectric Constant Fluorine and	)		
Carbon-Containing Silicon Oxide Dielectric	)		
Material Characterized by Improved Resistance	)		
to Oxidation"	)		

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.56

Honorable Commissioner of Patents and Trademarks Washington, D.C. 20231

August 29, 2003

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, Applicants submit the attached form PTO-1449 (modified). This application is a 37 C.F.R. 1.53(b) continuation application of Serial No. 09/792,691. Since all of the documents listed on the enclosed form PTO-1449 (modified) were previously cited to or by the USPTO in the prior application, under the provisions of 37 C.F.R. 1.98(d), copies of the listed documents are not enclosed.

Respectfully submitted,

Attorney for Applicants Registration No. 22,369

(909) 699-7551

Mailing Address:

Sandeep Jaggi, Chief Intellectual Property Counsel LSI Logic Corporation Legal Department - IP 1621 Barber Lane, Mail Stop D-106 Milpitas, CA 95035

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FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office  Docket No. Serial No.									
U.S. Depart	ment	of Commerce	00-643/1D						
INFOR	INFORMATION DISCLOSURE STATEMENT BY APPLICANT Applicants								
	(Use	several she	ets if nec	essary)	Sheldon A	ronowitz	et	al.	
					Filing Da Herewith	te		oup known	
			U.:	S. Patent Documents					
*Examiner Initial		Document Number	Date	Name	Class	Subclas	ss	Filing Da If Appropria	
	AA	5,874,367	2/23/99	Dobson	438	787			
	AB	6,028,015	2/22/00	Wang et al.	438	789		3/29/99	
	AC	6,114,259	9/5/00	Sukharev et al.	438	789		7/27/99	
	AD	6,147,012	11/14/00	Sukharev et al.	438	787		11/12/99	
	AE	6,043,167	3/28/00	Lee et al.	438	789		10/10/97	
	AF	5,314,845	5/24/94	Lee et al.	437	238		2/2/90	
	AG	5,915,203	6/22/99	Sengupta et al.	438	669		6/10/97	
	AH	6,365,528	4/2/02	Sukharev et al.	438	778	_	6/7/00	
	AI	5,571,571	11/5/96	Musaka et al.	427	574	_	6/14/94	
	AJ	6,303,047	10/16/01	Aronowitz et al.	252	1		3/22/99	
	AK	6,511,925	1/28/03	Aronowitz et al.	438	788		10/19/01	
			Fore	ign Patent Documents	3				
								Franslation	1
		Document Number	Date	Country	Class	Subclas	ss	Yes	No

## Document Number Country Class Subclass Yes No AL AN AO AO

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AR Bothra, S., et al., "Integration of 0.25 µm Three and Five Level Interconnect System for High Performance ASIC", 1997 Proceedings Fourteenth International VMIC Conference, Santa Clara, CA, June 10-12, 1997, pp.43-48.

AS Dobson, C.D., et al., "Advanced SiO2 Planarization Using Silane and H2O2", Semiconductor International, December 1994, pp. 85-88.

AT McClatchie, S., et al., "Low Dielectric Constant Oxide Films Deposited Using CVD Techniques", 1998 Proceedings Fourth International DUMIC Conference, February 16-17, 1998, pp. 311-318.

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

Date Considered

Examiner

FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office							Se	rial No.	
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*Examiner Initial		Document Number	Date	Name	Class	Subclas	ss	Filing Da If Appropria	
	ва	6,066,574	5,23/00	You et al.	438	781		11/6/98	
	вв	6,051,477	4/18/00	Nam	438	404		10/22/96	
	вс	6,025,263	2/15/00	Tsai et al.	438	624		9/11/97	
_	BD	5,939,763	8/17/99	Hao et al.	257	411		9/5/96	
	BE	5,864,172	1/26/99	Kapoor et al.	257	634		8/13/96	
	BF	5,688,724	11/18/97	Yoon et al.	437	235		12/23/94	
	BG	5,470,801	11/28/95	Kapoor et al.	437	238		6/28/93	
	вн	5,364,800	11/15/94	Joyner	437	28		6/24/93	
	BI	4,771,328	9/13/88	Malaviya et al.	357	49		11/24/86	
	BJ	3,652,331	3/28/72	Yamazaki	117	201		3/13/69	
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			Fore	eign Patent Documents	s				
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	вм								
	BN								
	во								
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	BR	BR Nguyen, S. et al., "Reaction Mechanisms of Plasma- and Thermal-Assisted Chemical Vapor Deposition of Tetraethylorthosilicate Oxide Films", <u>J. Electrochem. Soc.</u> , Vol. 137, No. 7, July, 1990, pp. 2209-2215.							
	BS	Semicondu	ıra, "Low-k ıctor Interi 122, and	Dielectrics: Will <u>national</u> , Vol. 23, N 124.	Spin-On or	CVD Pre	vai .qq	11?", . 108-110,	114,
	BT Peters, Laura, "Pursuing the Perfect Low-k Dielectric", Semiconductor  International, Vol. 21, No. 10, September, 1998, pp. 64-66, 68, 70, 72, and 74.					· ,			
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FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office  Sheet 3 of 4 sheets  Docket No. Serial No.									
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INFOR					Sheldon A			1	
	(US	e several she	eets 11 nec	essary)	Filing Da Herewith		Gr	oup	
			U.	S. Patent Documents					
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	CA	6,153,524	11/28/00	Henley et al.	438	691		7/28/98	
	СВ	6,051,073	4/18/00	Chu et al.	118	723		6/3/98	
	CC	5,580,429	12/3/96	Chan et al.	204	192.38		6/7/95	
	CD	5,558,718	9/24/96	Leung	118	723E		4/8/94	
	CE	5,628,871	5/13/97	Shinagawa	438	514		6/24/94	
	CF	6,204,192	3/20/01	Zhao et al.	438	723		3/29/99	
	CG	6,232,658	5/15/01	Catabay et al.	257	701		6/30/99	
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	CI	5,675,187	10/7/97	Numata et al.	257	758		5/16/96	
	CJ	5,559,367	9/24/96	Cohen et al.	257	77_		7/12/94	
	CK	5,376,595	12/27/94	Zupancic et al.	501	12		8/28/92	
			Fore	ign Patent Documents	3				
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	Document Number	Date	Country	Class	Subclass	Yes	No
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СМ							
CN							
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CP							

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CR	Sugahara, Satoshi, et al., "Chemical Vapor Deposition of CF3-Incorporated Silica Films for Interlayer Dielectric Application", 1999 Joint International Meeting, <u>Electrochemical Society Meeting Abstracts</u> , Vol. 99-2, 1999, Abstract No. 746.
cs	Koda, Seiichiro, et al., "A Study of Inhibition Effects for Silane Combustion by Additive Gases", <u>Combustion and Flame</u> , Vol. 73, No. 2, August, 1988, pp. 187-194.
СТ	

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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

FORM PTO-1449 (Modified) Docket No. Serial No. U.S. Department of Commerce, Patent and Trademark Office 00-643 Applicants INFORMATION DISCLOSURE STATEMENT BY APPLICANT Sheldon Aronowitz et al. (Use several sheets if necessary) Filing Date Group Herewith Unknown U.S. Patent Documents Document \*Examiner Filing Date Initial Number Date Name Class Subclass Appropriate 5,904,154 5/18/99 Chien et al. 1.2 DA 134 7/24/97 DB 5,882,489 3/16/99 Bersin et al. 204 192.35 4/26/96 1/12/99 Chao et al. 725 DC 5,858,879 438 6/6/97 DD 3,012,861 12/12/61 23 223.5 Ling 1/15/60 3,178,392 4/13/65 Kriner 260 46.5 4/9/62 DE DF 3,832,202 8/27/74 106 287 Ritchie 8/8/72 3,920,865 11/18/75 Läufer et al. 427 DG 220 4/6/72 DH 4,705,725 11/10/87 Glajch et al. 428 405 11/28/86 5,194,333 3/16/93 Ohnaka et al. DI 428 405 12/18/90 59 DJ 5,874,745 2/23/99 Kuo 257 8/5/97 DK Foreign Patent Documents Translation Class Subclass Document Date Country Yes No Number DE 198 04 7/1/99 Germany DT. H 01 L 21/312 Х 375 A1 EP 0 706 DM 4/10/96 Europe H 01 L 23/532 N/A 216 A2 EP 0 949 10/13/99 Europe H 01 L 21/312 N/A 663 A2 1/8/88 X-Abstract 63003437 DO Japan H 01 L 21/90 Only DP 8/19/99 PCT C 23 C N/A 99/41423 OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) DR DS DT Examiner Date Considered \*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.